

Features

- High speed
 - $t_{AA} = 8 \text{ ns}$
- Low active power
 - $I_{CC} = 225 \text{ mA}$ at 8 ns
- Low CMOS standby power
 - $I_{SB2} = 25 \text{ mA}$
- Operating voltages of $3.3 \pm 0.3\text{V}$
- 2.0V data retention
- Automatic power down when deselected
- TTL compatible inputs and outputs
- Easy memory expansion with \overline{CE}_1 , CE_2 , and \overline{CE}_3 features
- Available in Pb-free standard 119-Ball PBGA

Functional Description

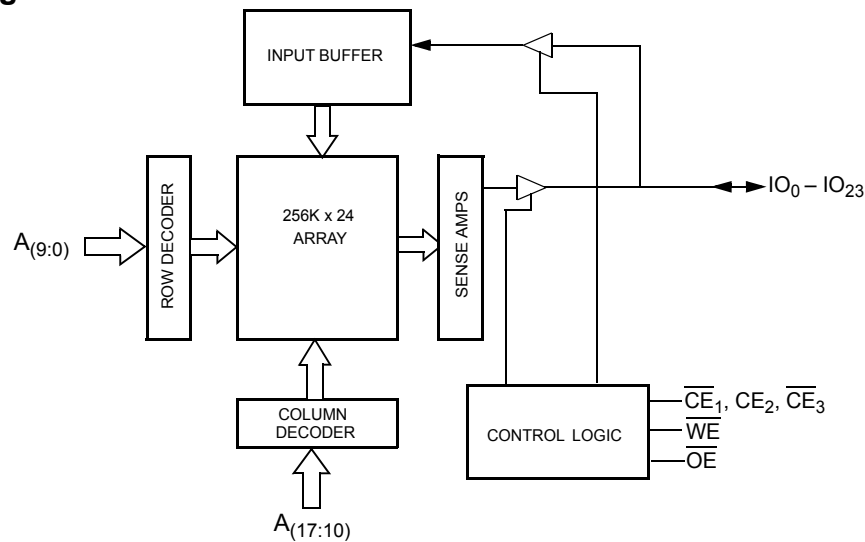
The CY7C1034DV33 is a high performance CMOS static RAM organized as 256K words by 24 bits. This device has an automatic power down feature that significantly reduces power consumption when deselected.

To write to the device, enable the chip (\overline{CE}_1 LOW, CE_2 HIGH, and \overline{CE}_3 LOW) while forcing the Write Enable (WE) input LOW.

To read from the device, enable the chip by taking \overline{CE}_1 LOW, CE_2 HIGH, and \overline{CE}_3 LOW, while forcing the Output Enable (OE) LOW and the Write Enable (WE) HIGH. See the Truth Table on page 7 for a complete description of Read and Write modes.

The 24 IO pins ($IO_0 - IO_{23}$) are placed in a high impedance state when the device is deselected (\overline{CE}_1 HIGH, CE_2 LOW, or \overline{CE}_3 HIGH) or when the output enable (\overline{OE}) is HIGH during a write operation. (\overline{CE}_1 LOW, CE_2 HIGH, \overline{CE}_3 LOW, and WE LOW).

Logic Block Diagram



Selection Guide

	-8	Unit
Maximum Access Time	8	ns
Maximum Operating Current	225	mA
Maximum CMOS Standby Current	25	mA

Pin Configuration
Figure 1. 119-Ball PBGA Top View ^[1]

	1	2	3	4	5	6	7
A	NC	A	A	A	A	A	NC
B	NC	A	A	\overline{CE}_1	A	A	NC
C	IO ₁₂	NC	CE ₂	A	\overline{CE}_3	NC	IO ₀
D	IO ₁₃	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₁
E	IO ₁₄	V _{SS}	V _{DD}	V _{SS}	V _{DD}	V _{SS}	IO ₂
F	IO ₁₅	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₃
G	IO ₁₆	V _{SS}	V _{DD}	V _{SS}	V _{DD}	V _{SS}	IO ₄
H	IO ₁₇	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₅
J	NC	V _{SS}	V _{DD}	V _{SS}	V _{DD}	V _{SS}	NC
K	IO ₁₈	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₆
L	IO ₁₉	V _{SS}	V _{DD}	V _{SS}	V _{DD}	V _{SS}	IO ₇
M	IO ₂₀	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₈
N	IO ₂₁	V _{SS}	V _{DD}	V _{SS}	V _{DD}	V _{SS}	IO ₉
P	IO ₂₂	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	IO ₁₀
R	IO ₂₃	NC	NC	NC	NC	NC	IO ₁₁
T	NC	A	A	\overline{WE}	A	A	NC
U	NC	A	A	\overline{OE}	A	A	NC

Note

1. NC pins are not connected on the die.

Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. These user guidelines are not tested.

- Storage Temperature -65°C to +150°C
- Ambient Temperature with Power Applied -55°C to +125°C
- Supply Voltage on V_{CC} Relative to GND ^[2]..... -0.5V to +4.6V
- DC Voltage Applied to Outputs in High Z State ^[2]..... -0.5V to V_{CC} + 0.5V

- DC Input Voltage ^[2] -0.5V to V_{CC} + 0.5V
- Current into Outputs (LOW) 20 mA
- Static Discharge Voltage..... >2001V (MIL-STD-883, Method 3015)
- Latch up Current..... >200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0°C to +70°C	3.3V ± 0.3V

DC Electrical Characteristics

Over the operating range

Parameter	Description	Test Conditions ^[3]	-8		Unit
			Min	Max	
V _{OH}	Output HIGH Voltage	V _{CC} = Min, I _{OH} = -4.0 mA	2.4		V
V _{OL}	Output LOW Voltage	V _{CC} = Min, I _{OL} = 8.0 mA		0.4	V
V _{IH}	Input HIGH Voltage		2.0	V _{CC} + 0.3	V
V _{IL} ^[2]	Input LOW Voltage		-0.3	0.8	V
I _{IX}	Input Leakage Current	GND ≤ V _I ≤ V _{CC}	-1	+1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _{OUT} ≤ V _{CC} , output disabled	-1	+1	μA
I _{CC}	V _{CC} Operating Supply Current	V _{CC} = Max, f = f _{MAX} = 1/t _{RC} , I _{OUT} = 0 mA CMOS levels		225	mA
I _{SB1}	Automatic CE Power Down Current — TTL Inputs	Max V _{CC} , $\overline{CE} \geq V_{IH}$, V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}		30	mA
I _{SB2}	Automatic CE Power Down Current — CMOS Inputs	Max V _{CC} , $\overline{CE} \geq V_{CC} - 0.3V$, V _{IN} ≥ V _{CC} - 0.3V, or V _{IN} ≤ 0.3V, f = 0		25	mA

Capacitance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	Max	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{CC} = 3.3V	8	pF
C _{OUT}	IO Capacitance		10	pF

Thermal Resistance

Tested initially and after any design or process changes that may affect these parameters.

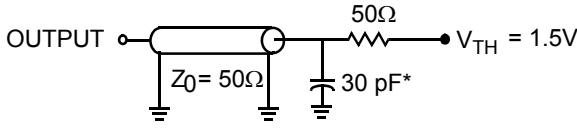
Parameter	Description	Test Conditions	119-Ball PBGA	Unit
θ _{JA}	Thermal Resistance (Junction to Ambient)	Still air, soldered on a 3 × 4.5 inch, four layer printed circuit board	20.31	°C/W
θ _{JC}	Thermal Resistance (Junction to Case)		8.35	°C/W

Notes

- 2. V_{IL} (min) = -2.0V and V_{IH} (max) = V_{CC} + 2V for pulse durations of less than 20 ns.
- 3. \overline{CE} refers to a combination of CE₁, CE₂, and CE₃. \overline{CE} is active LOW when CE₁ is LOW, CE₂ is HIGH, and CE₃ is LOW. \overline{CE} is HIGH when CE₁ is HIGH, CE₂ is LOW, or CE₃ is HIGH.

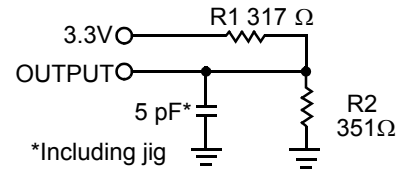
AC Test Loads and Waveform

The AC test loads and waveform diagram follows. [4]



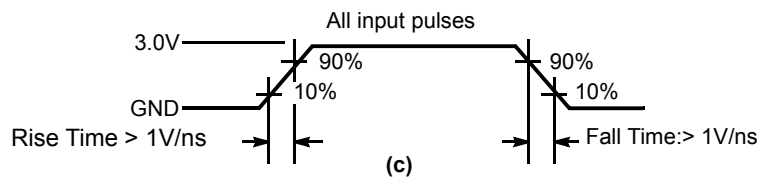
(a)

*Capacitive Load consists of all components of the test environment



(b)

*Including jig and scope



(c)

AC Switching Characteristics

Over the operating range [5]

Parameter	Description	-8		Unit
		Min	Max	
Read Cycle				
$t_{power}^{[6]}$	V_{CC} (Typical) to the First Access	100		μs
t_{RC}	Read Cycle Time	8		ns
t_{AA}	Address to Data Valid		8	ns
t_{OHA}	Data Hold from Address Change	3		ns
t_{ACE}	\overline{CE} Active LOW to Data Valid [3]		8	ns
t_{DOE}	\overline{OE} LOW to Data Valid		5	ns
t_{LZOE}	\overline{OE} LOW to Low Z [7]	1		ns
t_{HZOE}	\overline{OE} HIGH to High Z [7]		5	ns
t_{LZCE}	\overline{CE} Active LOW to Low Z [3, 7]	3		ns
t_{HZCE}	\overline{CE} Deselect HIGH to High Z [3, 7]		5	ns
t_{PU}	\overline{CE} Active LOW to Power Up [3, 8]	0		ns
t_{PD}	\overline{CE} Deselect HIGH to Power Down [3, 8]		8	ns

Notes

- Valid SRAM operation does not occur until the power supplies reach the minimum operating V_{DD} (3.0V). 100 μs (t_{power}) after reaching the minimum operating V_{DD} , normal SRAM operation begins including reduction in V_{DD} to the data retention (V_{CCDR} , 2.0V) voltage.
- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, and input pulse levels of 0 to 3.0V. Test conditions for the read cycle use output loading as shown in part a) of the AC Test Loads and Waveform, unless specified otherwise.
- t_{POWER} gives the minimum amount of time that the power supply is at typical V_{CC} values until the first memory access is performed.
- t_{HZOE} , t_{HZCE} , t_{LZOE} , t_{LZCE} , and t_{LZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ± 200 mV from steady state voltage.
- These parameters are guaranteed by design and are not tested.

AC Switching Characteristics (continued)

Over the operating range ^[5]

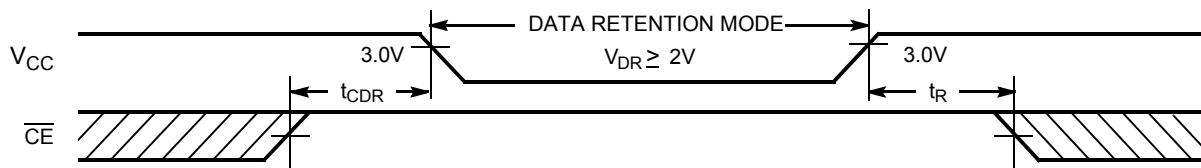
Parameter	Description	-8		Unit
		Min	Max	
Write Cycle ^[9, 10]				
t _{WC}	Write Cycle Time	8		ns
t _{SCE}	\overline{CE} Active LOW to Write End ^[3]	6		ns
t _{AW}	Address Setup to Write End	6		ns
t _{HA}	Address Hold from Write End	0		ns
t _{SA}	Address Setup to Write Start	0		ns
t _{PWE}	\overline{WE} Pulse Width	6		ns
t _{SD}	Data Setup to Write End	5		ns
t _{HD}	Data Hold from Write End	0		ns
t _{LZWE}	\overline{WE} HIGH to Low Z ^[7]	3		ns
t _{HZWE}	\overline{WE} LOW to High Z ^[7]		5	ns

Data Retention Characteristics

Over the operating range

Parameter	Description	Conditions ^[3]	Min	Typ	Max	Unit
V _{DR}	V _{CC} for Data Retention		2			V
I _{CCDR}	Data Retention Current	V _{CC} = 2V, CE ≥ V _{CC} - 0.2V, V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V			25	mA
t _{CDR} ^[11]	Chip Deselect to Data Retention Time		0			ns
t _R ^[12]	Operation Recovery Time		t _{RC}			ns

Data Retention Waveform



Notes

9. The internal write time of the memory is defined by the overlap of \overline{CE}_1 LOW, CE₂ HIGH, \overline{CE}_3 LOW, and \overline{WE} LOW. Chip enables must be active and \overline{WE} must be LOW to initiate a write and the transition of any of these signals terminates the write. The input data setup and hold timing are referenced to the leading edge of the signal that terminates the write.
10. The minimum write cycle time for Write Cycle No. 3 (\overline{WE} controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{SD}.
11. Tested initially and after any design or process changes that may affect these parameters.
12. Full device operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min)} ≥ 50 μs or stable at V_{CC(min)} ≥ 50 μs.

Switching Waveforms

Figure 2. Read Cycle No. 1 (Address Transition Controlled) [13, 14]

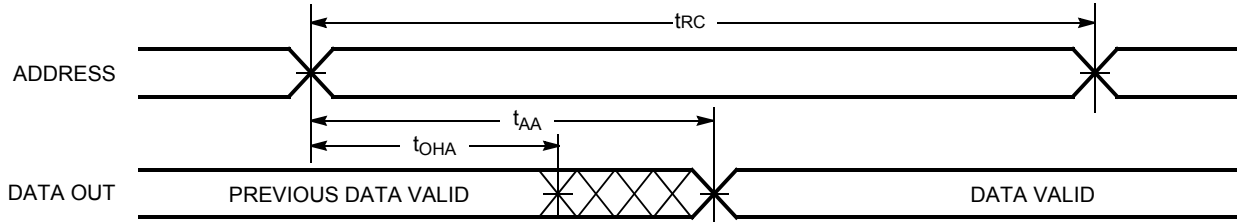


Figure 3. Read Cycle No. 2 (OE Controlled) [3, 14, 15]

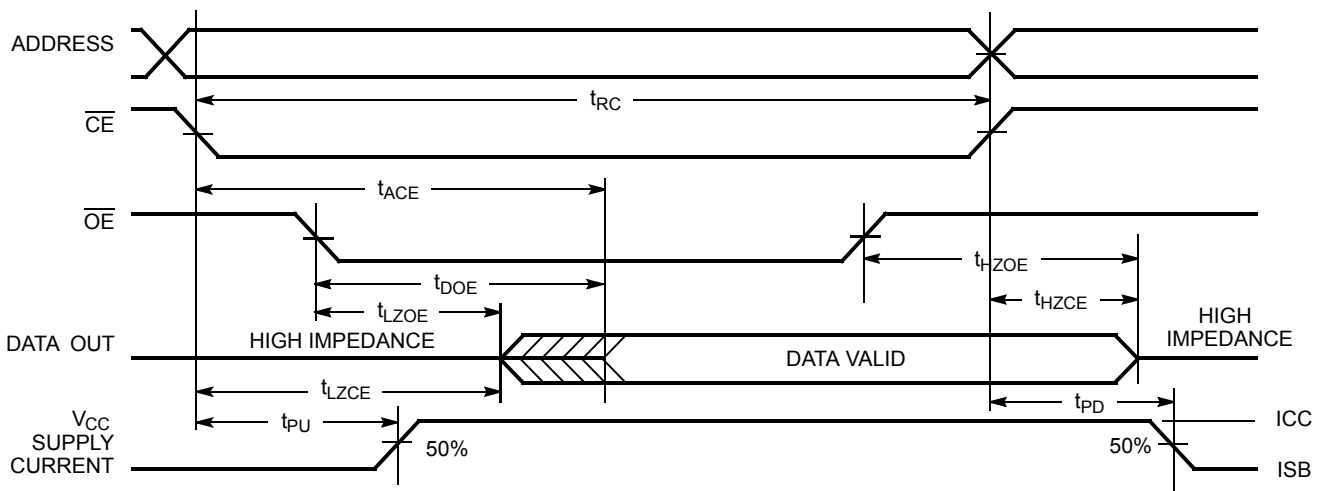
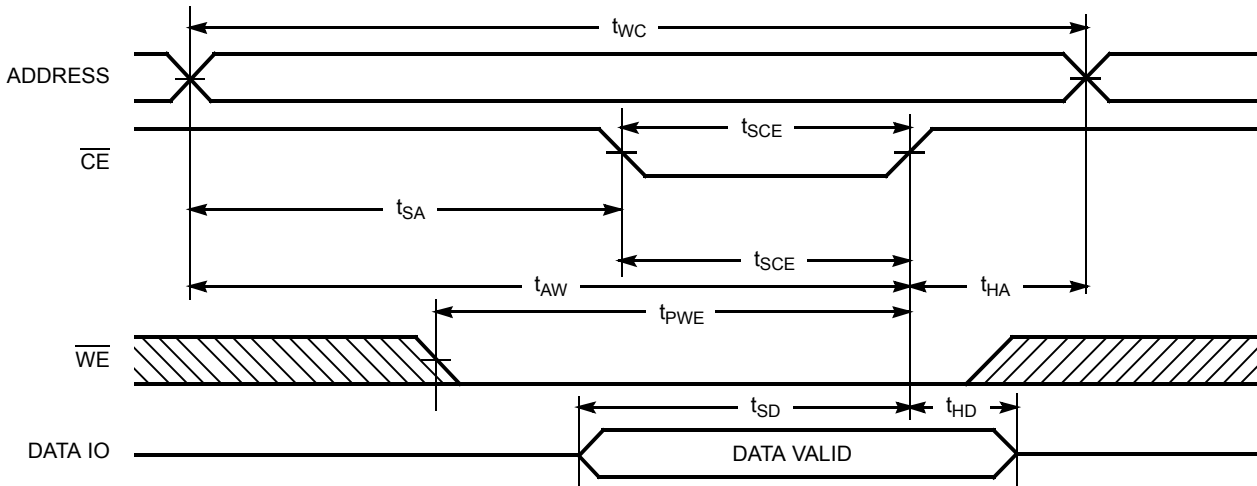


Figure 4. Write Cycle No. 1 (CE Controlled) [3, 16, 17]



Notes

- 13. Device is continuously selected. \overline{OE} , $\overline{CE} = V_{IL}$.
- 14. \overline{WE} is HIGH for read cycle.
- 15. Address valid before or similar to \overline{CE} transition LOW.
- 16. Data IO is high impedance if $\overline{OE} = V_{IH}$.
- 17. If \overline{CE} goes HIGH simultaneously with \overline{WE} going HIGH, the output remains in a high impedance state.

Switching Waveforms (continued)

Figure 5. Write Cycle No. 2 (\overline{WE} Controlled, \overline{OE} HIGH During Write) [3, 16, 17]

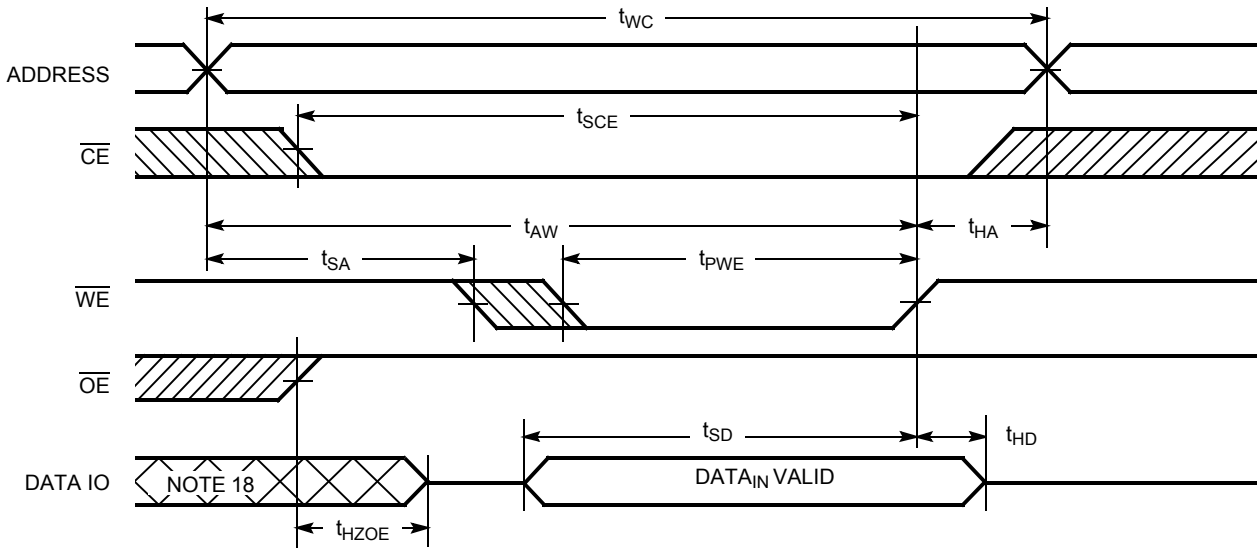
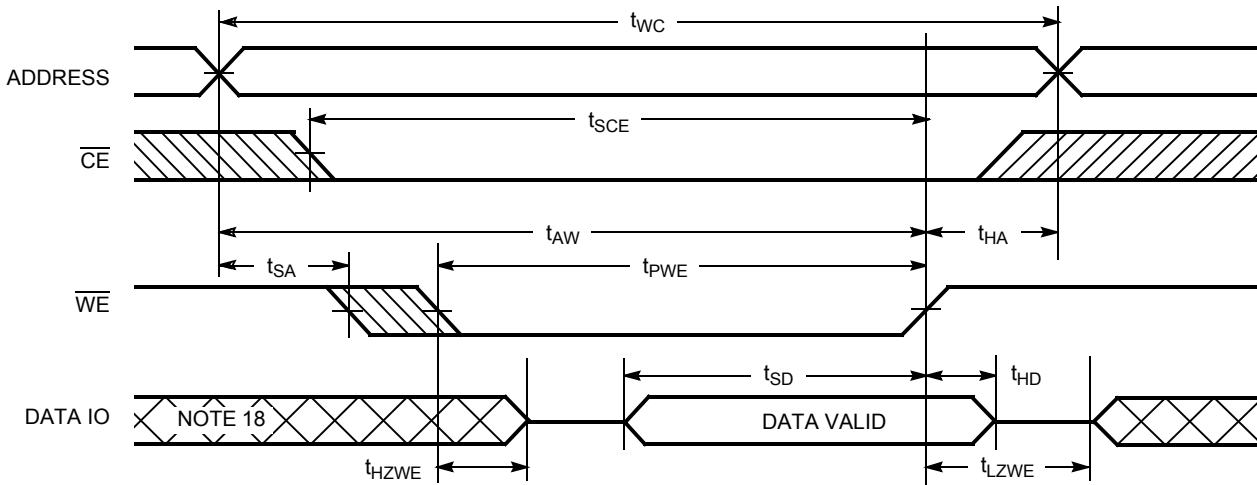


Figure 6. Write Cycle No. 3 (\overline{WE} Controlled, \overline{OE} LOW) [3, 17]



Truth Table

\overline{CE}_1	\overline{CE}_2	\overline{CE}_3	\overline{OE}	\overline{WE}	$IO_0 - IO_{23}$	Mode	Power
H	X	X	X	X	High Z	Power Down	Standby (I_{SB})
X	L	X	X	X	High Z	Power Down	Standby (I_{SB})
X	X	H	X	X	High Z	Power Down	Standby (I_{SB})
L	H	L	L	H	Full Data Out	Read	Active (I_{CC})
L	H	L	X	L	Full Data In	Write	Active (I_{CC})
L	H	L	H	H	High Z	Selected, Outputs Disabled	Active (I_{CC})

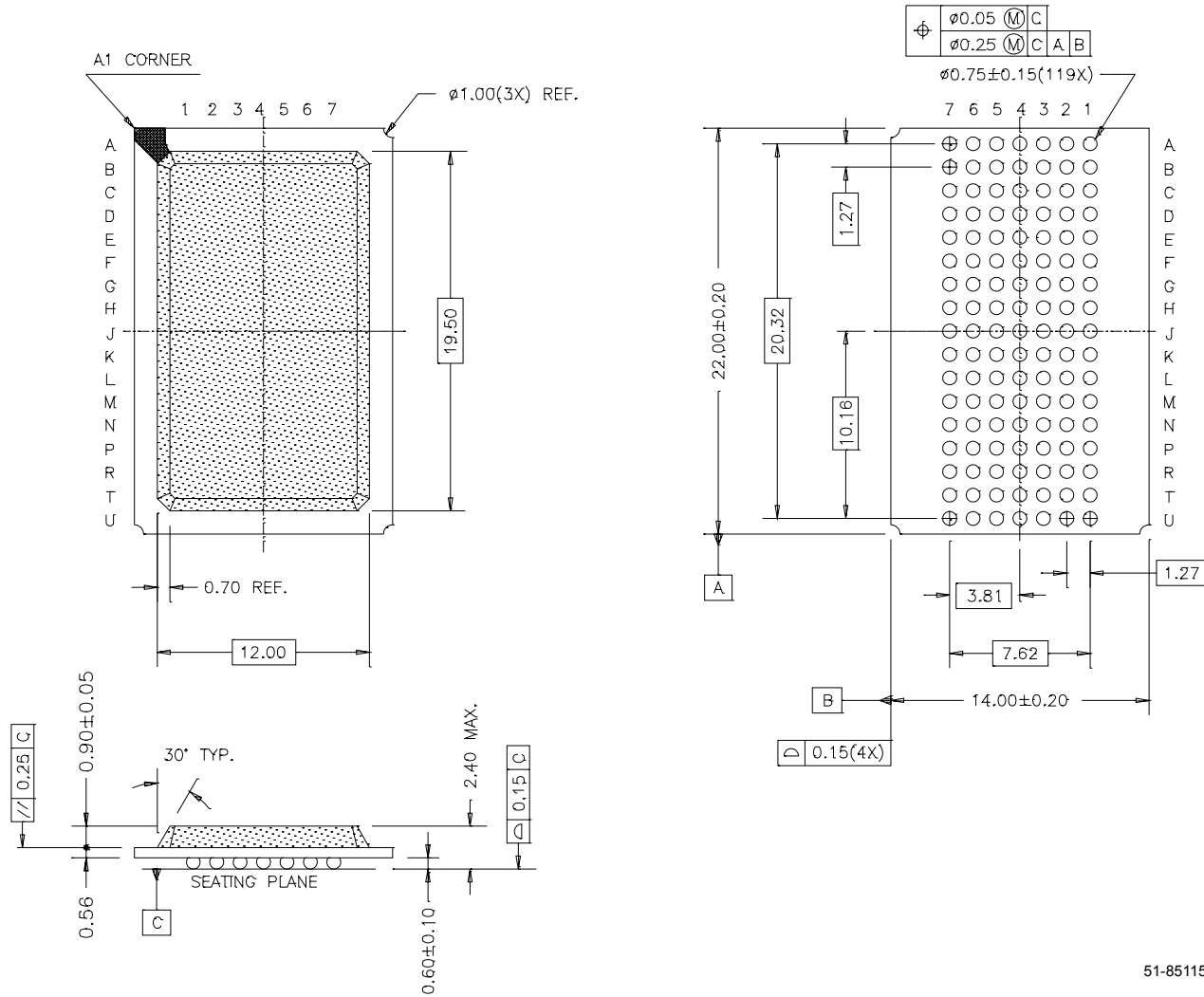
Note 18. During this period, the IOs are in the output state and input signals are not applied.

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
8	CY7C1034DV33-8BGXC	51-85115	119-Ball Plastic Ball Grid Array (14 x 22 x 2.4 mm) (Pb-Free)	Commercial

Package Diagram

Figure 7. 119-Ball PBGA (14 x 22 x 2.4 mm)



51-85115-*B

Document History Page

Document Title: CY7C1034DV33 6-Mbit (256K X 24) Static RAM				
Document Number: 001-08351				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	469517	See ECN	NXR	New datasheet
*A	499604	See ECN	NXR	Added note 1 for NC pins Changed I _{CC} specification from 150 mA to 185 mA Updated Test Condition for I _{CC} in DC Electrical Characteristics table Added note for t _{ACE} , t _{LZCE} , t _{HZCE} , t _{PU} , t _{PD} , t _{SCE} in AC Switching Characteristics Table on page 4
*B	1462586	See ECN	VKN/SFV	Converted from preliminary to final Updated block diagram Changed I _{CC} specification from 185 mA to 225 mA Updated thermal specs

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